ASSP for Power Supply Applications

(DC/DC converter for DSC/camcorder)

5 ch DC/DC Converter IC with Synchronous Rectification

MB39A108

■ DESCRIPTION

The MB39A108 is 5-channel DC/DC converter IC using pulse width modulation (PWM), and is suitable for up conversion, down conversion, and up/down conversion. The MB39A108 is built in 5 channels into TSSOP-38P/BCC-40P package and operates at 2 MHz maximum. Each channel can be controlled with soft-start.

The MB39A108 is suitable for power supply of high performance portable instruments such as DSC.

■ FEATURES

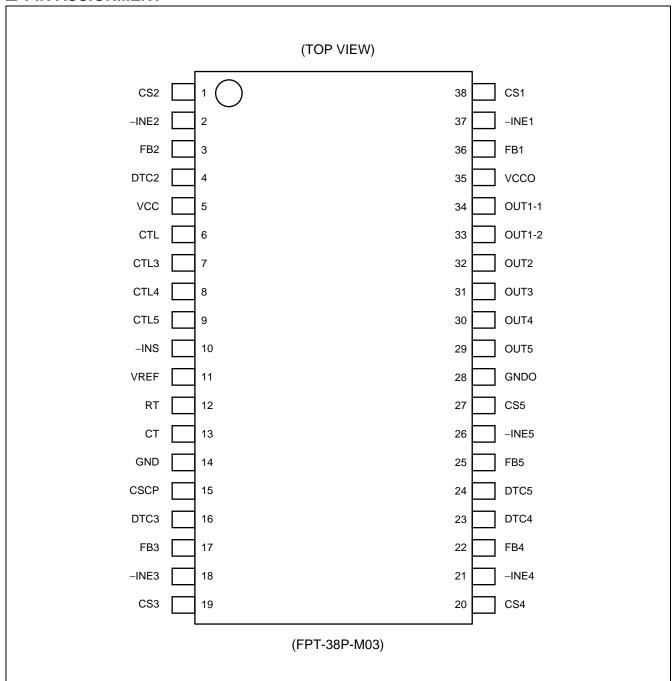
- Supports for down-conversion with synchronous rectification (CH1)
- Supports for down-conversion and up/down Zeta conversion (CH2, CH3)
- Supports for up-conversion and up/down Sepic conversion (CH4, CH5)
- Low voltage start-up (CH4, CH5): 1.7 V
- Power supply voltage range: 2.5 V to 11 V
- Reference voltage : 2.0 V ± 1%
- Error amplifier threshold voltage : 1.00 V \pm 1% (CH1), 1.23 V \pm 1% (CH2 to CH5)
- Oscillation frequency range: 200 kHz to 2.0 MHz
- Standby current : 0 μA (Typ)
- · Built-in soft-start circuit independent of loads
- Built-in totem-pole type output for MOS FET
- Short-circuit detection capability by external signal (INS terminal)
- Two types of package (TSSOP-38 pin : 1 type, BCC-40 pin : 1 type)

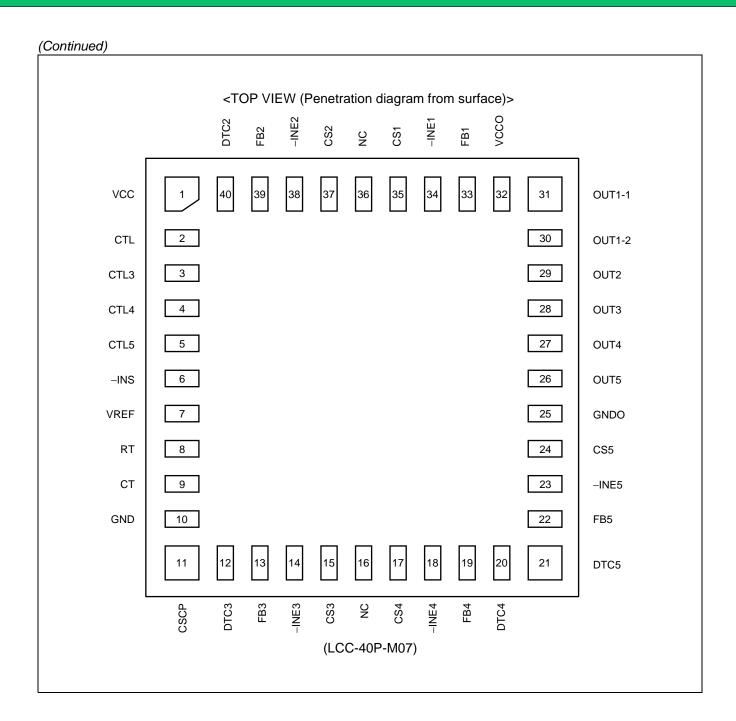
■ APPLICATIONS

- Digital still camera (DSC)
- Digital video camera (DVC)
- Surveillance camera etc



■ PIN ASSIGNMENT





■ PIN DESCRIPTION

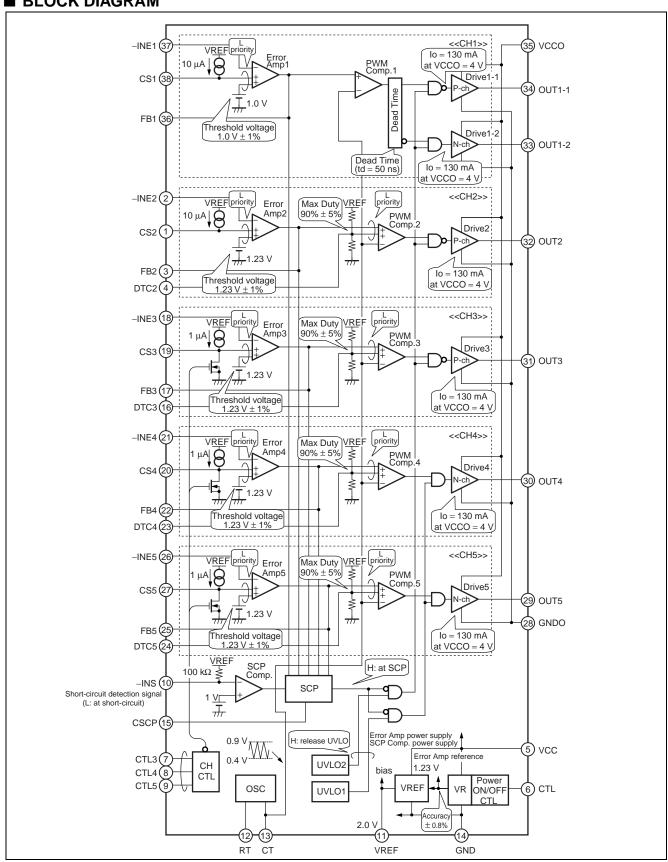
	Pin I	No.			
Block	PK	G	Pin name	I/O	Description
	TSSOP	всс	†		
	36	33	FB1	0	Error amplifier output terminal.
	37	34	- INE1		Error amplifier inverted input terminal.
	38	35	CS1	_	Soft-start setting capacitor connection terminal.
CH1	34	31	OUT1-1	0	P-ch drive output terminal (External main side FET gate driving).
	33	30	OUT1-2	0	N-ch drive output terminal (External synchronous rectification side FET gate driving).
	4	40	DTC2	ı	Dead time control terminal.
	3	39	FB2	0	Error amplifier output terminal
CH2	2	38	- INE2		Error amplifier inverted input terminal.
	1	37	CS2	_	Soft-start setting capacitor connection terminal.
	32	29	OUT2	0	P-ch drive output terminal.
	16	12	DTC3	I	Dead time control terminal.
	17	13	FB3	0	Error amplifier output terminal
СНЗ	18	14	- INE3		Error amplifier inverted input terminal.
	19	15	CS3	_	Soft-start setting capacitor connection terminal.
	31	28	OUT3	0	P-ch drive output terminal.
	23	20	DTC4	I	Dead time control terminal.
	22	19	FB4	0	Error amplifier output terminal.
CH4	21	18	- INE4	I	Error amplifier inverted input terminal.
	20	17	CS4		Soft-start setting capacitor connection terminal.
	30	27	OUT4	0	N-ch drive output terminal.
	24	21	DTC5		Dead time control terminal.
	25	22	FB5	0	Error amplifier output terminal.
CH5	26	23	- INE5	I	Error amplifier inverted input terminal.
	27	24	CS5		Soft-start setting capacitor connection terminal.
	29	26	OUT5	0	N-ch drive output terminal.
OSC	13	9	СТ		Triangular wave frequency setting capacitor connection terminal.
	12	8	RT		Triangular wave frequency setting resistor connection terminal.

(Continued)

	Pin I	No.				
Block	Block PKG		Pin name	I/O	Description	
TSSOP		всс	1			
	6	2	CTL		Power supply control terminal.	
	7	3	CTL3	ı	CH3 control terminal.	
Control	8	4	CTL4		CH4 control terminal.	
Control	9 5		CTL5		CH5 control terminal.	
	15	11	CSCP		Short-circuit detection circuit capacitor connection terminal.	
	10	6	– INS	ı	Short-circuit detection comparator inverted input terminal.	
	35	32	VCCO	_	Drive output block power supply terminal.	
	5	1	VCC		Power supply terminal.	
Power	11	7	VREF	0	Reference voltage output terminal.	
	28	25	GNDO		Drive output block ground terminal.	
	14 10		GND		Ground terminal.	

Note: The terminal number which has been described in the text is the one of the TSSOP-38P package after this.

■ BLOCK DIAGRAM



■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Conditions	Rati	Unit		
raiailletei	Symbol	Conditions	Min	Max	Oilit	
Power supply voltage	Vcc	VCC, VCCO terminal	_	12	V	
Output current	lo	OUT1 to OUT5 terminal	_	20	mA	
Peak output current	Іор	OUT1 to OUT5 terminal Duty ≤ 5% (t = 1/fosc × Duty)	_	400	mA	
Dower dissination	Po	Ta ≤ + 25 °C (TSSOP-38P)	_	1680*1	mW	
Power dissipation	PD	Ta ≤ + 25 °C (BCC-40P)	_	1020*2	mW	
Storage temperature	Тѕтѕ	_	- 55	+ 125	°C	

^{*1 :} When mounted on a 76 mm \times 76 mm \times 1.6 mm FR-4 boards.

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

^{*2 :} When mounted on a 117 mm \times 84 mm \times 0.8 mm FR-4 boards.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Conditions		Value		Unit
Farameter	Symbol	Conditions	Min	Тур	Max	Ullit
Start power supply voltage	Vcc	VCC, VCCO terminal (CH4, CH5)	1.7	_	11	V
Power supply voltage	Vcc	VCC, VCCO terminal (CH1 to CH5)	2.5	4	11	V
Reference voltage output current	IREF	VREF terminal	– 1		0	mA
	VINE	- INE1 to - INE5 terminal	0		Vcc - 0.9	V
Input voltage	VINE	- INS terminal	0	_	V _{REF}	V
	VDTC	DTC2 to DTC5 terminal	0		V _{REF}	V
Control input voltage	Vctl	CTL, CTL3 to CTL5 terminal	0		11	V
Output current	lo	OUT1 to OUT5 terminal	- 15		+ 15	mΑ
Oscillation frequency	fosc	*	0.2	0.97	2.0	MHz
Timing capacitor	Ст	_	27	100	680	pF
Timing resistor	R⊤	_	3.0	6.8	39	kΩ
Soft-start capacitor	Cs	CS1 to CS5 terminal		0.1	1.0	μF
Short-circuit detection capacitor	Cscp	_		0.1	1.0	μF
Reference voltage output capacitor	Cref	_		0.1	1.0	μF
Operating ambient temperature	Та	_	- 30	+ 25	+ 85	°C

^{*:} Refer to "SETTING THE TRIANGULAR WAVE OSCILLATION FREQUENCY".

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

> Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

> No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their representatives beforehand.

■ ELECTRICAL CHARACTERISTICS

(VCC = VCCO = 4 V, Ta = +25 °C)

Danama	4	0	Dia Na	Canditions		Value		11:4:4
Parame	eter	Symbol	Pin No.	Conditions	Min	Тур	Max	Unit
		V _{REF1}	11	VREF = 0 mA	1.98	2.00	2.02	V
	Output voltage	V _{REF2}	11	Vcc = 2.5 V to 11 V	1.975	2.000	2.025	V
	voltage	V _{REF3}	11	VREF = 0 mA to -1 mA	1.975	2.000	2.025	V
Reference	Input stability	Line	11	Vcc = 2.5 V to 11 V		2*		mV
voltage block [VREF]	Load stability	Load	11	VREF = 0 mA to -1 mA		2*		mV
[[VKEF]	Temperature stability	ΔV _{REF} /	11	Ta = 0 °C to + 85 °C		0.20*		%
	Short-circuit output current	los	11	VREF = 0 V		- 130*		mA
Under voltage lockout protection	Threshold voltage	Vтн	34	VCC =	1.7	1.8	1.9	V
circuit block (CH1 to CH3)	Hysteresis width	Vн	34	_	0.05	0.1	0.2	V
[UVLO1_3]	Reset voltage	Vrst	34	VCC = Y	1.55	1.7	1.85	V
Under voltage lockout protection	Threshold voltage	Vтн	30	VCC =	1.35	1.5	1.65	V
circuit block (CH4, CH5)	Hysteresis width	Vн	30	_	0.02	0.05	0.1	V
[UVLO4_5]	Reset voltage	Vrst	30	VCC = Y	1.27	1.45	1.63	V
Short-circuit detection block	Threshold voltage	Vтн	15	_	0.65	0.70	0.75	V
[SCP]	Input source current	ICSCP	15	_	- 1.4	- 1.0	- 0.6	μΑ
	Oscillation	fosc ₁	29 to 34	$C_T = 100 \text{ pF}, R_T = 6.8 \text{ k}\Omega$	0.92	0.97	1.02	MHz
Triangular wave	frequency	fosc2	29 to 34	$C_{T} = 100 \; pF, \; R_{T} \; = 6.8 \; k\Omega \label{eq:ct}$ Vcc = 2.5 V to 11 V	0.917	0.97	1.023	MHz
oscillator block	Frequency input stability	Δfosc/ fosc	29 to 34	$C_T = 100 \; pF, \; R_T \; = 6.8 \; k\Omega \label{eq:ct}$ Vcc = 2.5 V to 11 V	_	1.0*	_	%
-	Frequency temperature stability	Δfosc/ fosc	29 to 34	$C_T = 100 \text{ pF}, R_T = 6.8 \text{ k}\Omega$ Ta = 0 °C to + 85 °C	_	1.0*	_	%
Soft-start block (CH1, CH2) [CS1, CS2]	Charge current	Ics	1, 38	CS1, CS2 = 0 V	- 13	- 10	-7	μА
Soft-start block (CH3 to CH5) [CS3 to CS5]	Charge current	Ics	19, 20, 27	CS3 to CS5 = 0 V	- 1.3	- 1.0	- 0.7	μА

^{*:} Standard design value

(VCC = VCCO = 4 V, Ta = +25 °C)

Doromatar				0 1111		Value		Ī
Para	ameter	Symbol	Pin No.	Conditions	Min	Тур	Max	Unit
	Throubold voltage	V _{TH1}	37	Vcc = 2.5 V to 11 V Ta = +25 °C	0.990	1.000	1.010	V
	Threshold voltage	V _{TH2}	37	Vcc = 2.5 V to 11 V Ta = 0 °C to + 85 °C	0.988	1.000	1.012	V
	Temperature stability	ΔVтн/ Vтн	37	Ta = 0 °C to $+85$ °C		0.1*	_	%
	Input bias current	lв	37	- INE1 = 0 V	- 120	- 30	_	nA
Error amp block (CH1)	Voltage gain	Av	36	DC		100*		dB
[Error Amp1]	Frequency bandwidth	BW	36	Av = 0 dB		1.4*		MHz
	Output voltage	Vон	36	_	1.7	1.9	_	V
	Output voltage	Vol	36	_	_	40	200	mV
	Output source current	Isource	36	FB1 = 0.65 V		- 2	- 1	mA
	Output sink current	Isink	36	FB1 = 0.65 V	150	200	_	μА
	Throshold voltage	V _{TH1}	2, 18, 21, 26	Vcc = 2.5 V to 11 V Ta = +25 °C	1.217	1.230	1.243	V
	Threshold voltage	V _{TH2}	2, 18, 21, 26	Vcc = 2.5 V to 11 V Ta = 0 °C to + 85 °C	1.215	1.230	1.245	V
	Temperature stability	ΔVтн/ Vтн	2, 18, 21, 26	Ta = 0 °C to $+85$ °C		0.1*	_	%
	Input bias current	lв	2, 18, 21, 26	- INE2 to - INE5 = 0 V	- 120	- 30	_	nA
Error amp block (CH2 to CH5)	Voltage gain	Av	3, 17, 22, 25	DC		100*	_	dB
[Error Amp2 to Error Amp5]	Frequency bandwidth	BW	3, 17, 22, 25	Av = 0 dB		1.4*		MHz
	Output voltage	Vон	3, 17, 22, 25	_	1.7	1.9	_	٧
	Output voltage	VoL	3, 17, 22, 25	_		40	200	mV
	Output source current	ISOURCE	3, 17, 22, 25	FB2 to FB5 = 0.65 V	_	- 2	- 1	mA
	Output sink current	İsink	3, 17, 22, 25	FB2 to FB5 = 0.65 V	150	200		μА

^{*:} Standard design value

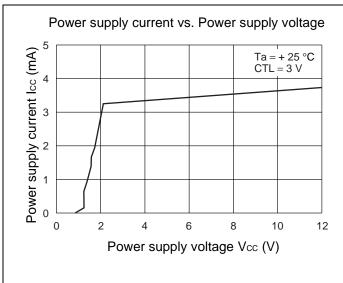
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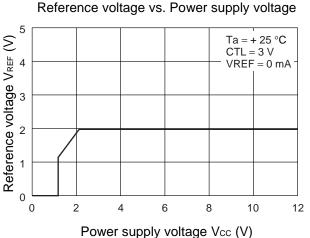
(VCC = VCCO = 4 V, Ta = +25 °C)

Parameter		Symbol	Pin No.	Conditions		Value		Unit
Paraili	etei	Symbol	Pin No.	Conditions	Min	Тур	Max	Onit
PWM compara-	Threshold	Vто	33, 34	Duty cycle = 0%	0.35	0.4	0.45	V
tor block (CH1) [PWM Comp.1]	voltage	V _{T100}	33, 34	Duty cycle = 100%	0.85	0.9	0.95	V
PWM compara-	Threshold	V _{т0}	29 to 32	Duty cycle = 0%	0.35	0.4	0.45	V
tor block (CH2 to CH5)	voltage	V _{T100}	29 to 32	Duty cycle = 100%	0.85	0.9	0.95	V
[PWM Comp.2 to PWM Comp.5]	Maximum duty cycle	Dtr	29 to 32	$C_T = 100 \text{ pF},$ $R_T = 6.8 \text{ k}\Omega$	85	90	95	%
	Output source current	Isource	29 to 34	Duty ≤ 5% (t = 1/fosc × Duty) OUT = 0 V	_	- 130	- 75	mA
Output block (CH1 to CH5)	Output sink current	İsink	29 to 34		75	130		mA
[Drive1 to Drive5]	Output on resistor	Rон	29 to 34	OUT = - 15 mA		18	27	Ω
		Rol	29 to 34	OUT = 15 mA		18	27	Ω
	Dead time	t _{D1}	t _{D1} 33, 34 OUT2 \(\frac{1}{2} - \text{OUT1} \(\frac{1}{2} \)		_	50*		ns
		t D2	33, 34	OUT1 _ OUT2 _	_	50*		ns
Short-circuit detection block	Threshold voltage	Vтн	34	_	0.97	1.00	1.03	V
[SCP Comp.]	Input bias current	lв	10	- INS = 0 V	- 25	- 20	- 17	μА
Control block	Output on condition	Vıн	6, 7 to 9	CTL, CTL3 to CTL5	1.5		11	V
(CTL, CTL3 to CTL5)	Output off condition	VıL	6, 7 to 9	CTL, CTL3 to CTL5	0		0.5	V
[CTL, CHCTL]	Input ourrent	Істьн	6, 7 to 9	CTL, CTL3 to CTL5 = 3 V	5	30	60	μΑ
	Input current	ICTLL	6, 7 to 9	CTL, CTL3 to CTL5 = 0 V	_	_	1	μΑ
	Standby	Iccs	5	CTL, CTL3 to CTL5 = 0 V	_	0	2	μА
General	current	Iccso	35	CTL = 0 V		0	1	μА
	Power supply current	Icc	5	CTL = 3 V		4	6	mA

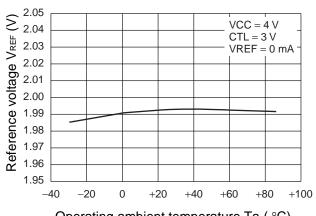
^{*:} Standard design value

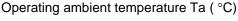
■ TYPICAL CHARACTERISTICS

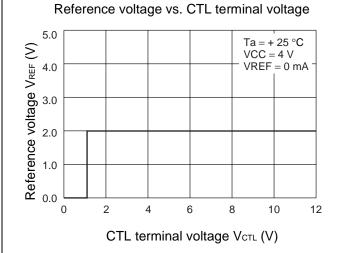


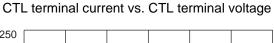


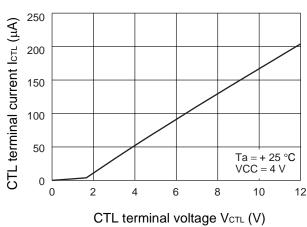
Reference voltage vs. Operating ambient temperature

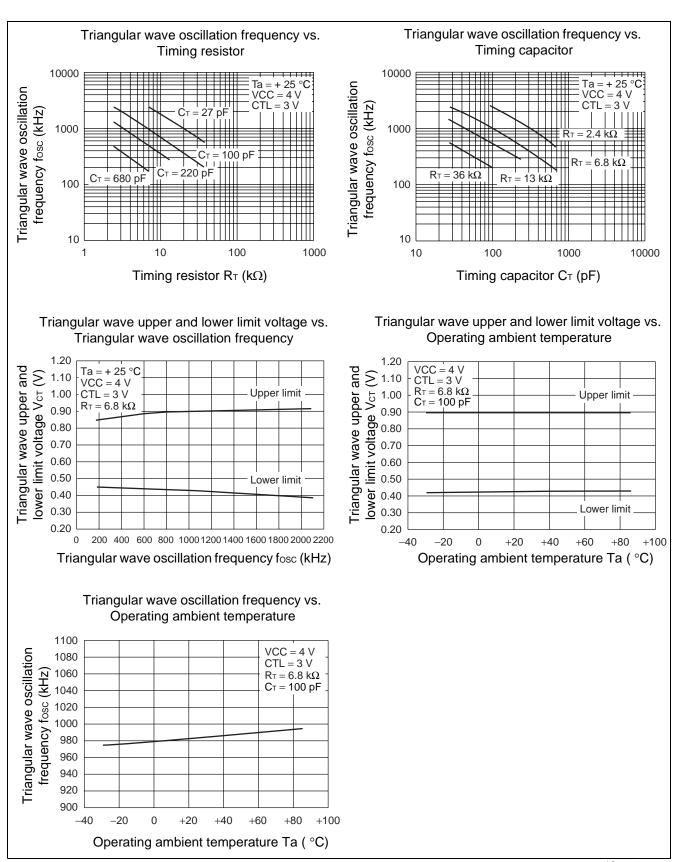


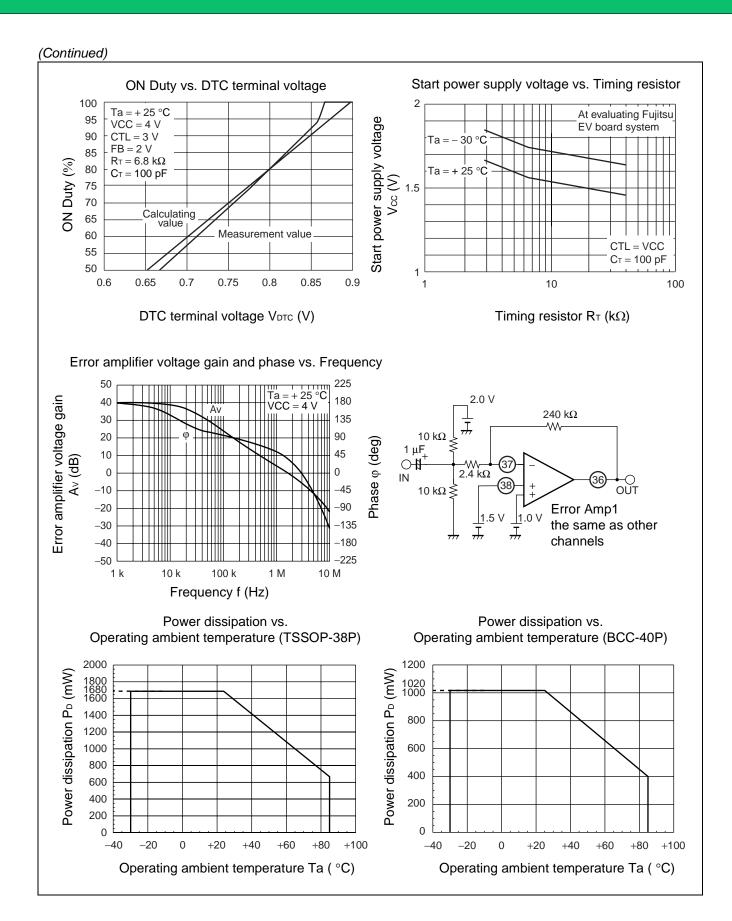












■ FUNCTIONAL DESCRIPTION

1. DC/DC Converter Function

(1) Reference voltage block (VREF)

The reference voltage circuit generates the reference voltage (2.0 V Typ) to which it makes amends for the temperature by the voltage supplied by the power supply terminal (pin 5). It is used as a reference in IC voltage.

It is also possible to supply the load current of up to 1 mA to external device as a output reference voltage through the VREF terminal (pin 11).

(2) Triangular wave oscillator block (OSC)

The triangular wave oscillator block generates the triangular wave oscillation waveforms of amplitude 0.4 V to 0.9 V by connecting the timing capacitor for and timing resistor to the CT terminal (pin 13) and RT terminal (pin 12) respectively.

The triangular wave is input to the PWM comparator in the IC.

(3) Error amplifier block (Error Amp1 to Error Amp5)

The error amplifier detects output voltage of DC/DC converter and outputs PWM control signals.

In addition, an arbitrary loop gain can be set by connecting a feedback resistor and capacitor from the output terminal to inverted input terminal of the error amplifier, enabling stable phase compensation to the system.

The CS1 terminal (pin 38) to CS5 terminal (pin 27) that are non-inverted input terminal of error amplifier can prevent rush currents at power supply startup, by connecting a soft-start capacitor. The soft-start time is detected by the error amplifier, which provides a constant soft-start time independent of output load of DC/DC converter.

Also, it is possible to prevent rush current at power supply start-up by connecting a soft-start capacitor with CS1 terminal (pin 38) to CS5 terminal (pin 27) which are the non-inverted input terminal for Error Amp. The use of Error Amp for soft-start detection makes it possible for a system to operate on a fixed soft-start time that is independent of the output load on the DC/DC converter.

(4) PWM comparator block (PWM Comp.1 to PWM Comp.5)

The PWM comparator block is a voltage-pulse width converter that controls the output duty depending on the input/output voltage.

When the error amplifier output voltage and DTC voltage remain higher than the triangular wave voltage, output transistor is turned on.

(5) Output block (Drive1 to Drive5)

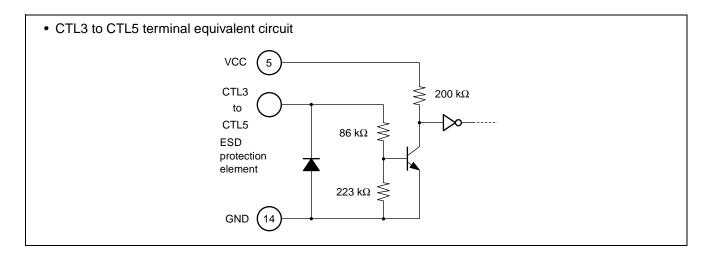
The output block is in the totem-pole type, capable of driving an external P-ch MOS FET (CH1 main side, and CH2 and CH3) and N-ch MOS FET (CH1 synchronous rectification side, and CH4 and CH5).

2. Channel Control Function

Main and each channel are set to ON/OFF by CTL terminal (pin 6), CS1 terminal (pin 38), CS2 terminal (pin 1), CTL3 terminal (pin 7), CTL4 terminal (pin 8), and CTL5 terminal (pin 9).

CTL	CS1	CS2	CTL3	CTL4	CTL5	Power	CH1	CH2	CH3	CH4	CH5
L	Х	Х	Х	Х	Х	OFF	Stops	Stops	Stops	Stops	Stops
<u>H</u>	GND	GND	L	L	L	<u>ON</u>	Stops	Stops	Stops	Stops	Stops
H	<u>HiZ</u>	GND	L	L	L	<u>ON</u>	Operation	Stops	Stops	Stops	Stops
H	GND	<u>HiZ</u>	L	L	L	<u>ON</u>	Stops	Operation	Stops	Stops	Stops
<u>H</u>	GND	GND	<u>H</u>	L	L	<u>ON</u>	Stops	Stops	Operation	Stops	Stops
H	GND	GND	L	<u>H</u>	L	<u>ON</u>	Stops	Stops	Stops	Operation	Stops
H	GND	GND	L	L	<u>H</u>	<u>ON</u>	Stops	Stops	Stops	Stops	Operation
<u>H</u>	<u>HiZ</u>	<u>HiZ</u>	<u>H</u>	<u>H</u>	<u>H</u>	<u>ON</u>	Operation	Operation	Operation	Operation	Operation

Note: Note that current over stand-by current flows into VCC terminal when the CTL terminal is in "L" level and one of terminals between CTL3 to CTL5 is set to "H" level (Refer to "● CTL3 to CTL5 terminal equivalent circuit").



3. Protection Function

(1) Timer-latch short-circuit protection circuit (SCP, SCP Comp.)

The short-circuit detection comparator (SCP) detects the output voltage level of each channel, and if any channel output voltage becomes the short-circuit detection voltage or less, the timer circuits are actuated to start charging the external capacitor Cscp connected to the CSCP terminal (pin 15).

When the capacitor (Cscp) voltage reaches about 0.7 V, the circuit is turned off the output transistor and sets the dead time to 100%.

In addition, the short-circuit detection from external input is capable by using –INS terminal (pin 10) on short-circuit detection comparator (SCP Comp.) .

To release the actuated protection circuit, either turn the power supply off and on again or set the CTL terminal (pin 6) to the "L" level to lower the VREF terminal (pin 11) voltage to 1.27 V (Min) or less (Refer to "■ SETTING TIME CONSTANT FOR TIMER-LATCH SHORT-CIRCUIT PROTECTION CIRCUIT").

(2) Under voltage lockout protection circuit block (UVLO)

The transient state or a momentary decrease in the power supply voltage, which occurs when the power supply is turned on, may cause the IC to malfunction, resulting in breakdown or degradation of the system. To prevent such malfunctions, under voltage lockout protection circuit detects a decrease in internal reference voltage with respect to the power supply voltage, turned off the output transistor, and set the dead time to 100 % while holding the CSCP terminal (pin 15) at "L" level.

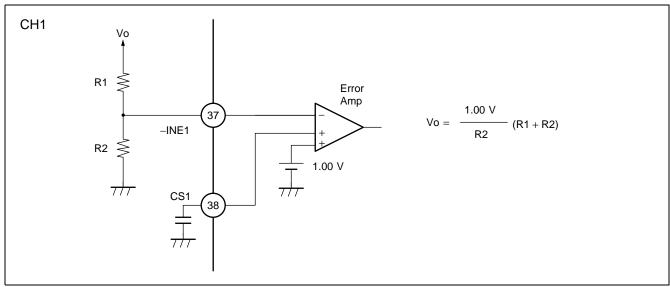
The circuit restores the output transistor to normal when the power supply voltage reaches the threshold voltage of the under-voltage lockout protection circuit.

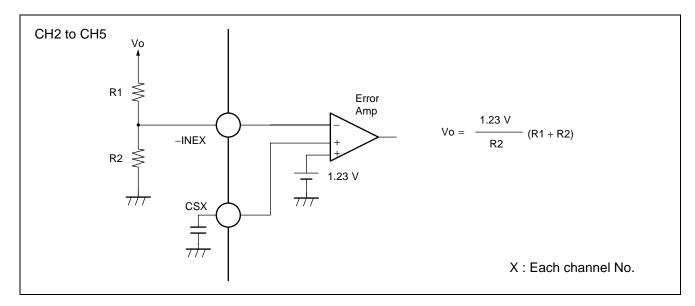
■ PROTECTION CIRCUIT OPERATING FUNCTION TABLE

This table refers to output condition when protection circuit is operating.

·						
Operation circuit	OUT1-1	OUT1-2	OUT2	OUT3	OUT4	OUT5
Short-circuit protection circuit	<u>H</u>	L	<u>H</u>	<u>H</u>	L	L
Under voltage lockout protection circuit	<u>H</u>	L	<u>H</u>	<u>H</u>	L	L

■ SETTING THE OUTPUT VOLTAGE





■ SETTING THE TRIANGULAR WAVE OSCILLATION FREQUENCY

The triangular wave oscillation frequency can be set by the timing resistor (R_T) connected to the RT terminal (pin 12) and the timing capacitor (C_T) connected to the CT terminal (pin 13).

Triangular wave oscillation frequency: fosc

fosc (kHz)
$$\Rightarrow \frac{659600}{C_T (pF) \times R_T (k\Omega)}$$

■ SETTING THE SOFT-START TIME

To prevent rush currents when the IC is turned on, you can set a soft-start by connecting soft-start capacitors (Cs1 to Cs5) to the CS1 terminal (pin 38) to CS5 terminal (pin 27) respectively.

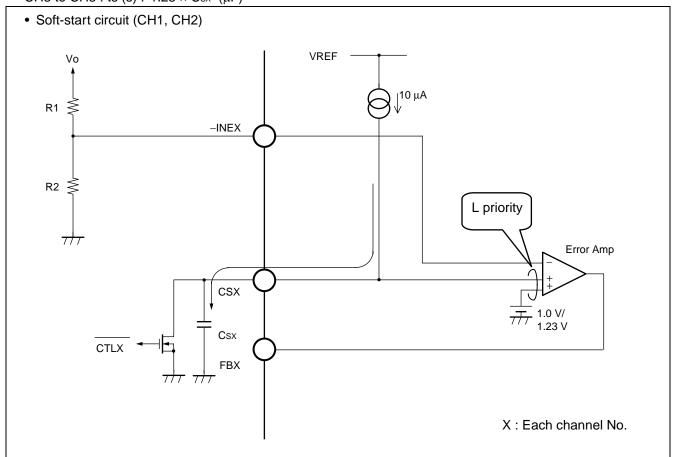
As shown in the figure below, changing $\overline{\text{CTLX}}$ from "H" to "L" in the CH1 and CH2 circuits causes the external soft-start capacitors (C_{S1} and C_{S2}) connected to CS1 and CS2 terminals to start charging with a current approximately 10 μ A.

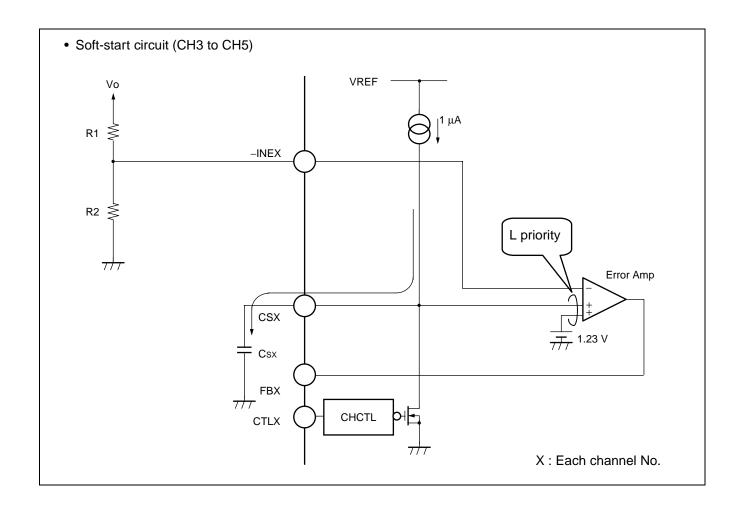
As shown in the figure on the next page, changing CTLX from "L" to "H" in the CH3 to CH5 circuits causes the external soft-start capacitors connected to CS3 to CS5 terminals to start charging with a current of approximately 1 μ A.

The error amplifier output (FB1 to FB5) is determined by comparison between the lower voltage of the two non-inverted input terminal voltage (1.23 V (CH: 1.0 V), CS terminal voltages) and the inverted input terminal voltage (-INE1 to -INE5). The FB terminal voltage is decided for the soft-start period (CS terminal voltage < 1.23 V (CH: 1.0 V)) by the comparison between -INE terminal voltage and CS terminal voltage. The DC/DC converter output voltage rises in proportion to the CS terminal voltage as the soft-start capacitor externally connected to the CS terminal is charged. The soft-start time is obtained from the following formula:

Soft-start time: ts(time to output 100%)

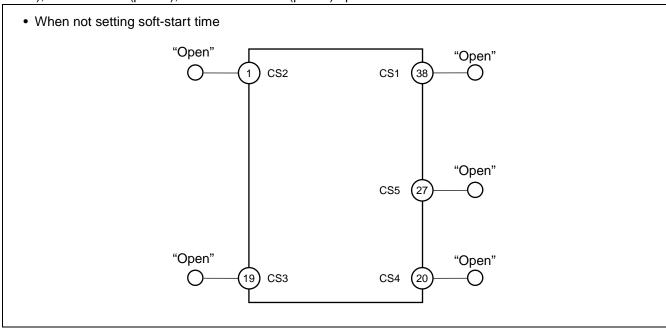
CH1 : ts (s) \Rightarrow 0.100 \times Csx (μ F) CH2 : ts (s) \Rightarrow 0.123 \times Csx (μ F) CH3 to CH5 : ts (s) \Rightarrow 1.23 \times Csx (μ F)





■ PROCESSING WHEN NOT USING CS TERMINAL

When soft-start function is not used, leave the CS1 terminal (pin 38), CS2 terminal (pin 1), CS3 terminal (pin 19), CS4 terminal (pin 20), and CS5 terminal (pin 27) open.



■ SETTING TIME CONSTANT FOR TIMER-LATCH SHORT-CIRCUIT PROTECTION CIRCUIT

Each channel uses the short-circuit detection comparator (SCP Comp.) to always compare the error amplifier's output level to the reference voltage.

While DC/DC converter load conditions are stable on all channels, the short-circuit detection comparator output remains at "L" level, and the CSCP terminal (pin 15) is held at "L" level.

If the load condition on a channel changes rapidly due to a short-circuit of the load, causing the output voltage to drop, the output of the short-circuit detection comparator on that channel goes to "H" level. This causes the external short-circuit protection capacitor Cscp connected to the CSCP terminal to be charged at 1 μ A.

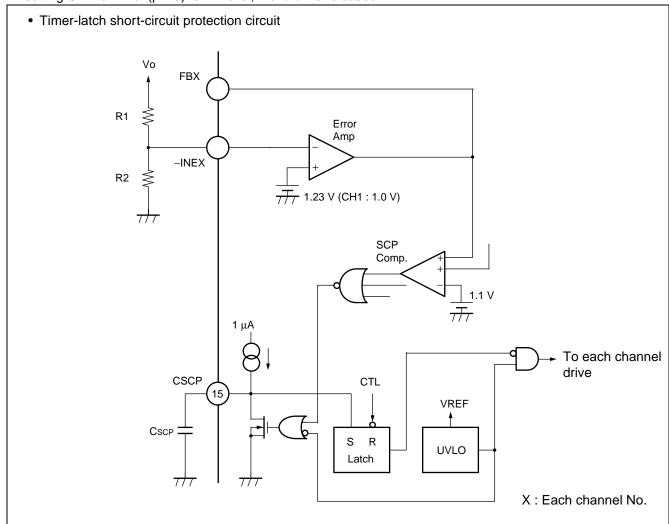
Short-circuit detection time: tcscp

tcscp (s)
$$\Rightarrow$$
 0.70 \times Cscp (μ F)

When the capacitor Cscp is charged to the threshold voltage ($V_{TH} \neq 0.7V$), the latch is set to and the external FET is turned off (dead time is set to 100%). At this time, the latch input is closed and CSCP terminal (pin 15) is held at "L" level.

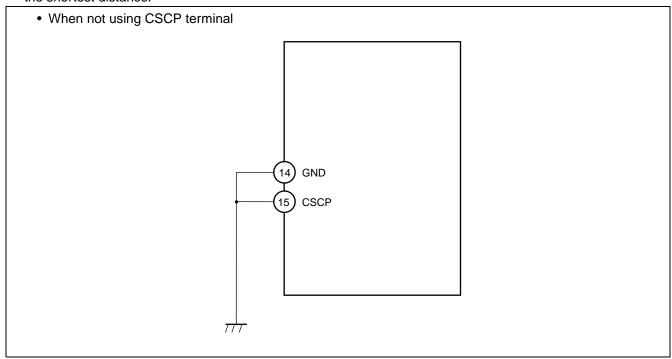
In addition, the short-circuit detection from external input is capable by using –INS terminal (pin 10) on the short-circuit detection comparator (SCP Comp.) . The short-circuit detection operation starts when –INS terminal voltage is less than threshold voltage ($V_{TH} \neq 1 \text{ V}$) .

When the power supply is turn off and on again or VREF terminal (pin 11) voltage is less than 1.27 V (Min) by setting CTL terminal (pin 6) to "L" level, the latch is released.



■ PROCESSING WHEN NOT USING CSCP TERMINAL

When not using the timer-latch short-circuit protection circuit, connect the CSCP terminal (pin 15) to GND with the shortest distance.

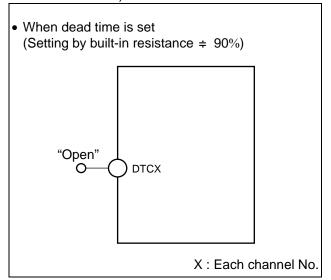


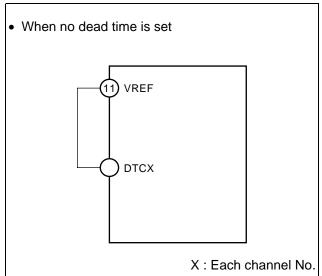
■ SETTING THE DEAD TIME

When the device is set for step-up or inverted output based on the step-up, step-up/down Zeta conversion, step-up/down Sepic conversion, or flyback conversion, the FB terminal voltage may reach and exceed the triangular wave voltage due to load fluctuation. If this is the case, the output transistor is fixed to a full-ON state (ON duty = 100 %). To prevent this, set the maximum duty of the output transistor.

When the DTC terminal is opened, the maximum duty is 90% (Typ) because of this IC built-in resistance which sets the DTC terminal voltage.

When the DTC terminal is not used, connect it directly to the VREF terminal (pin 11) as shown below (when no dead time is set).





Set the DTC terminal voltage by resistance divider from VREF terminal voltage when you change the maximum duty by external resistance (Refer to "• When dead time is set (Setting by external resistance)").

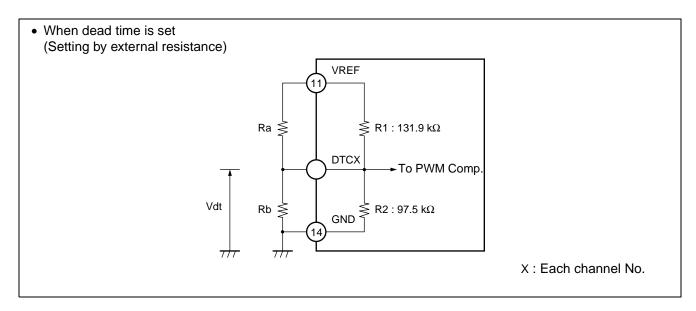
When the DTC terminal voltage is higher than the triangular wave voltage, the output transistor is turned on. The maximum duty calculation formula assuming that triangular wave amplitude : = 0.5 V and triangular wave lower voltage : = 0.4 V is given below.

It is possible to set DTC terminal voltage (dead time) by disregarding built-in resistance (include the tolerance) by adjusting external resistance to 1/10 or less of built-in resistance. Set to become 1mA or less in total of each channel the load current of VREF terminal.

DUTY (ON) Max
$$\Rightarrow \frac{\text{Vdt} - 0.4 \text{ V}}{0.5 \text{ V}} \times 100 \text{ (%)}^*$$

$$Vdt = \frac{Rb}{Ra + Rb} \times VREF \text{ (condition : } Ra < \frac{R1}{10} \text{ , } Rb < \frac{R2}{10} \text{)}$$

* : DUTY obtained by the above-mentioned formula is a calculated value. For setting, refer to "ON Duty vs. DTC terminal voltage" in ■ TYPICAL CHARACTERISTICS.



Example setting : For an aim Max duty (ON) of 80% (Vdt = 0.8 V) with Ra = 13.7 k Ω and Rb = 9.1 k Ω

Calculation using external resistors Ra and Rb only

$$Vdt = \frac{Rb}{Ra + Rb} \times VREF \doteqdot 0.80 \text{ V}$$

$$DUTY (ON) \text{ Max} \doteqdot \frac{Vdt - 0.4 \text{ V}}{0.5 \text{ V}} \times 100 \text{ (\%)} \doteqdot 80\%^* \cdots [1]$$

Calculation considering internal resistor (tolerance ± 20%) also

$$Vdt = \frac{\text{(Rb and R2 combined resistance)}}{\text{(Ra and R1 combined resistance)}} \times \text{VREF} \\ \div 0.80 \text{ V} \\ \pm 0.13\%$$

$$DUTY \text{(ON) Max} \\ \div \frac{\text{Vdt} - 0.4 \text{ V}}{0.5 \text{ V}} \times 100 \text{ (\%)} \\ \div 80\% \\ \pm 0.2\%^* \\ \cdots \text{[2]}$$

*: Based on [1] and [2] above, selecting external resistances of 1/10th or less of the built-in resistance enables the built-in resistance to be ignored.

As for the duty difference, please expect \pm 5% (at fosc = 1 MHz) . It is because of being with the difference of a triangular wave amplitude.

■ OPERATION EXPLANATION WHEN CTL TURNING ON AND OFF

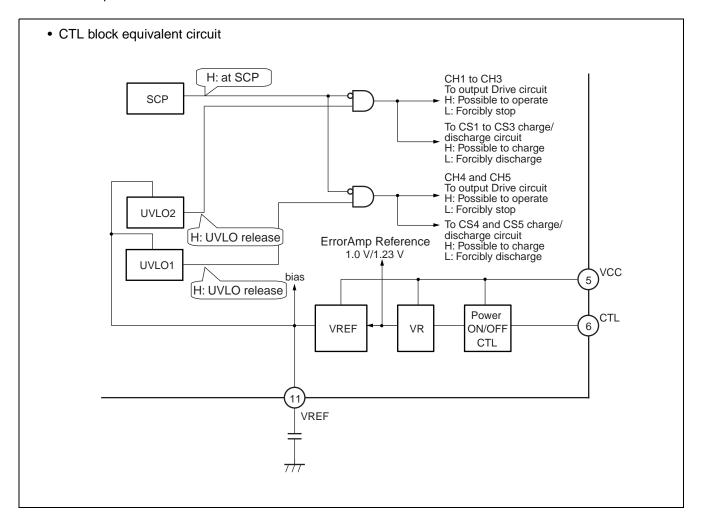
When CTL is turned on, internal reference voltage VR and VREF generate. When VREF exceeds each threshold voltage (VTH1,VTH2) of UVLO1 and UVLO2 (under voltage lockout protection circuit), UVLO1 and UVLO2 are released, and the operation of output drive circuit of each channel becomes possible.

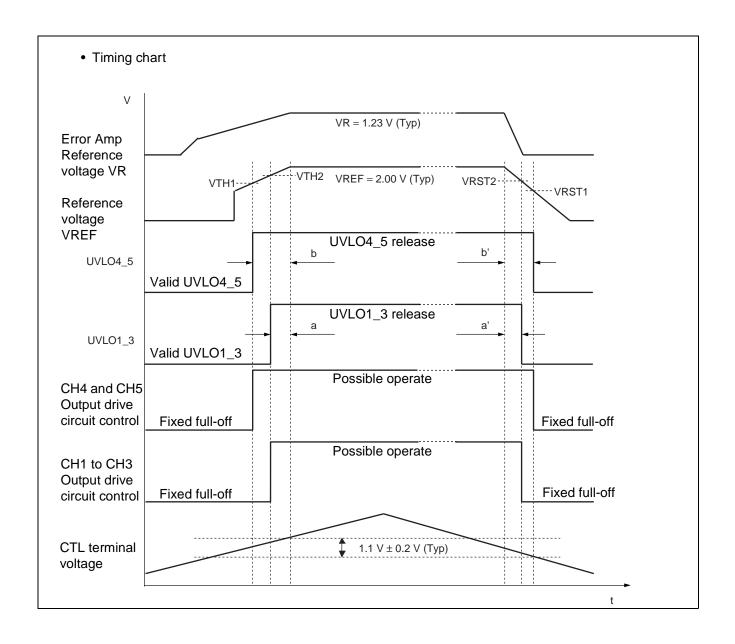
When CTL is off, VR and VREF fall. When VREF decreases and UVLO1 and UVLO2 fall below each reset voltage (VRST1,VRST2), UVLO operates and output Drive circuit of each channel is forcibly done the operation stop, and makes the output off state.

When period to reaching to 2.0 V by VREF voltage after UVLO1 and UVLO2 are released by turning on CTL (refer to a and b in "• Timing chart") and VREF decreases from 2.0 V after turning off CTL and the period until do the operation of UVLO1 and UVLO2(refer to a' and b' in "• Timing chart"), the bias voltage and the bias current in IC do not reach a prescribed value because VREF which is the reference voltage does not reach 2.0 V, and the speed of response for IC has decreased.

Moreover, when it does the turning on and off of the input sudden change, the load sudden change, and CTL3 to CTL5 in this period, IC cannot conform and the output might overshoot.

Therefore, impress the voltage to CTL terminal by which the VREF terminal voltage never stays in the above-mentioned period.





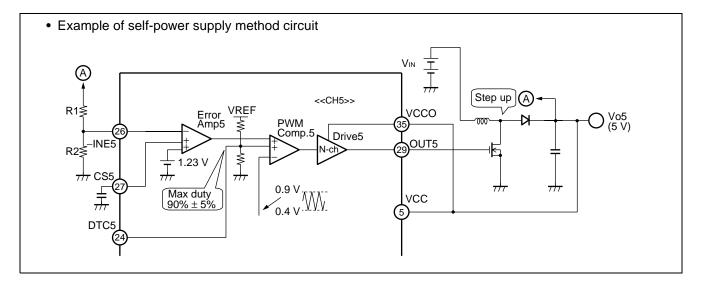
■ ABOUT THE LOW VOLTAGE OPERATION

1.7 V or more is necessary for the VCC terminal and the VCCO terminal for the self-power supply type to use the step-up circuit as the start voltage.

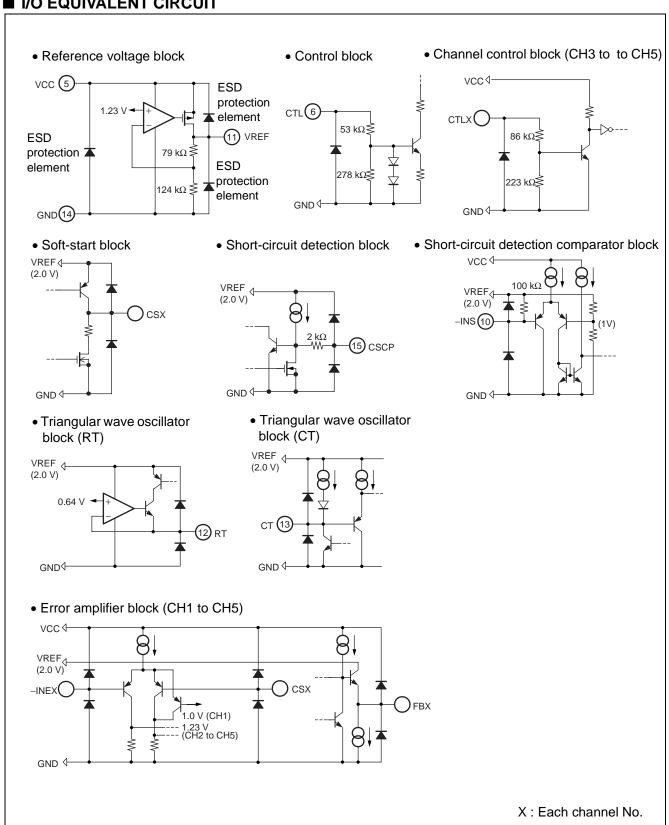
Even if V_{IN} decreases up to 1.5 V afterwards, it is possible to operate if the VCC terminal voltage and the VCCO terminal voltage rise to 2.5 V or more after start-up.

However, it is necessary not to exceed the maximum duty set value by the duty due to the VIN decrease.

Include other channels, and confirm an enough operation margin when using it.

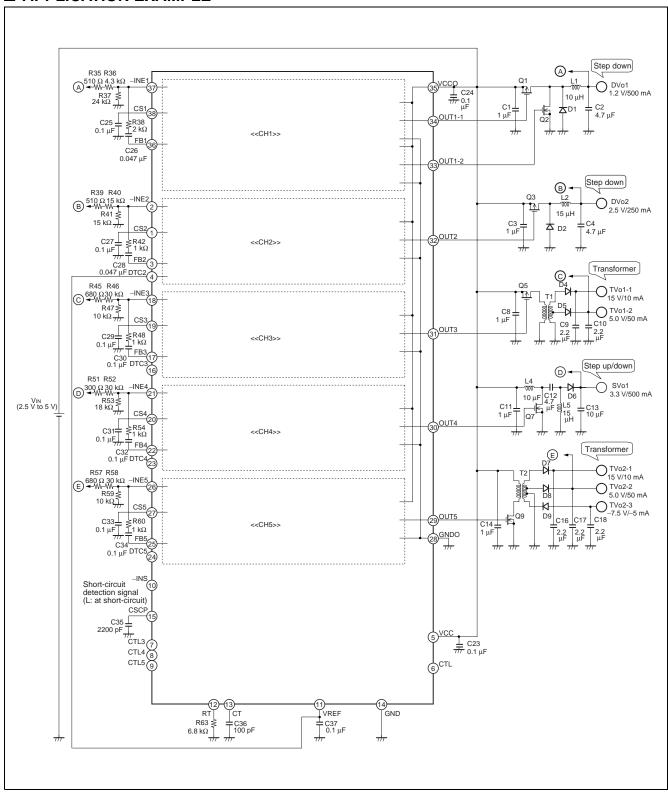


■ I/O EQUIVALENT CIRCUIT



PMW comparator block Output block (CH1 to CH5) FB2 to FB5 DTCX GNDQ X : Each channel No.

■ APPLICATION EXAMPLE



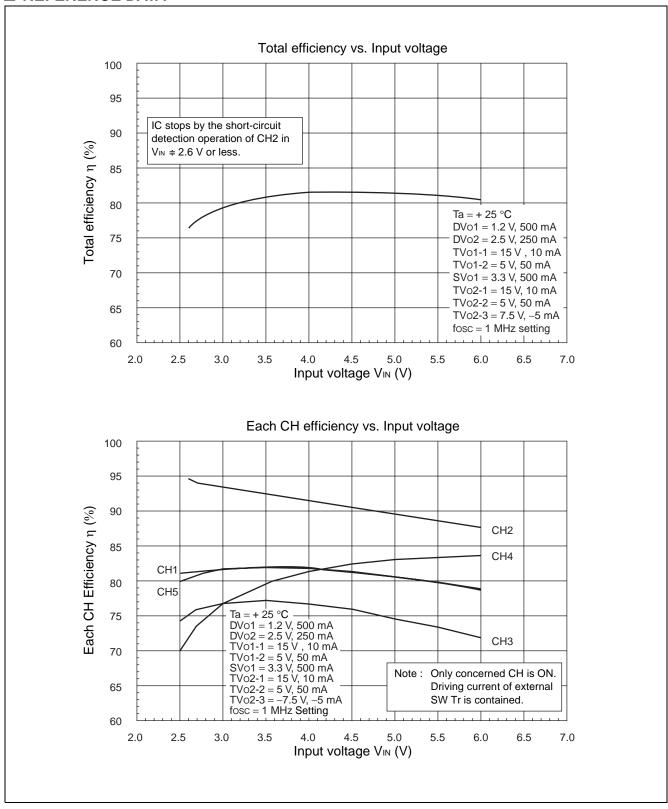
■ PARTS LIST

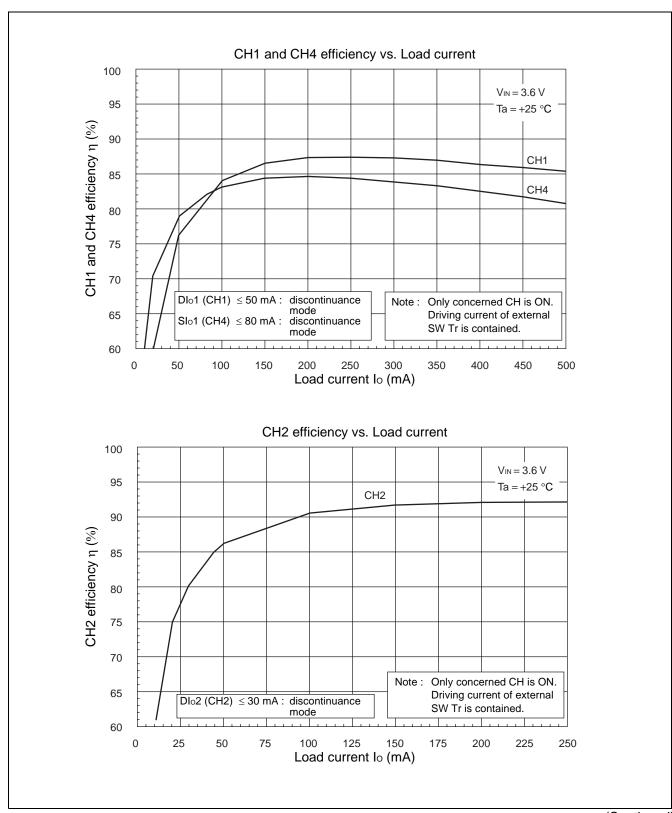
COMPONENT	ITEM	SPECIF	ICATION	VENDOR	PARTS No.
Q1, Q3	P-ch FET	VDS = 20 \	V, ID = - 1.5 A	SANYO	MCH3317
Q2, Q7, Q9	N-ch FET		V, ID = 1.8 A	SANYO	MCH3405
Q5	P-ch FET		V, ID = - 2 A	SANYO	MCH3306
D1, D2, D6	Diode		lax), at IF = 1 A	SANYO	SBS004
D4, D5, D7 to D9	Diode		ax), at IF = 0.5 A	SANYO	SB05-05CP
L1, L4 L2, L5	Inductor Inductor	10 μH 15 μH	0.94 A, 56 mΩ 0.76 A, 97 mΩ	TDK TDK	RLF5018T- 100MR94 RLF5018T- 150MR76
T1, T2	Transformer			SUMIDA	CLQ52 5388-T138
C1, C3	Ceramics Condenser	1 μF	25 V	TDK	C3216JB1E105K
C2, C4, C12	Ceramics Condenser	4.7 μF	16 V	TDK	C3216JB1C475K
C8, C11	Ceramics Condenser	1 μF	25 V	TDK	C3216JB1E105K
C9, C10	Ceramics Condenser	2.2 μF	25 V	TDK	C3216JB1E225K
C13	Ceramics Condenser	10 μF	6.3 V	TDK	C3216JB0J106K
C14	Ceramics Condenser	1 μF	25 V	TDK	C3216JB1E105K
C16 to C18	Ceramics Condenser	2.2 μF	25 V	TDK	C3216JB1E225K
C23 to C25, C27	Ceramics Condenser	0.1 μF	50 V	TDK	C1608JB1H104K
C26, C28 C29 to C34	Ceramics Condenser Ceramics Condenser	0.1 μF 0.047 μF 0.1 μF	50 V 50 V 50 V	TDK TDK TDK	C1608JB1H473K C1608JB1H104K
C35	Ceramics Condenser	2200 pF	50 V	TDK	C1608JB1H222K
C36	Ceramics Condenser	100 pF	50 V	TDK	C1608CH1H101J
C37	Ceramics Condenser	0.1 μF	50 V	TDK	C1608JB1H104K
R35, R39	Resistor	510 Ω	0.5%	ssm	RR0816P-511-D
R36	Resistor	4.3 kΩ	0.5%	ssm	RR0816P-432-D
R37	Resistor	24 kΩ	0.5%	ssm	RR0816P-243-D
R38	Resistor	2 kΩ	0.5%	ssm	RR0816P-202-D
R40, R41	Resistor	15 kΩ	0.5%	ssm	RR0816P-153-D
R42, R48, R54	Resistor	1 kΩ	0.5%		RR0816P-102-D
R45, R57	Resistor	680 Ω	0.5%	ssm	RR0816P-681-D
R46, R52, R58	Resistor	30 kΩ	0.5%	ssm	RR0816P-303-D
R47, R59	Resistor	10 kΩ	0.5%	ssm	RR0816P-103-D
R51	Resistor	300 Ω	0.5%	ssm	RR0816P-301-D
R53	Resistor	18 kΩ	0.5%	ssm	RR0816P-183-D
R60	Resistor	1 kΩ	0.5%		RR0816P-102-D
R63	Resistor	6.8 kΩ	0.5%	ssm	RR0816P-682-D

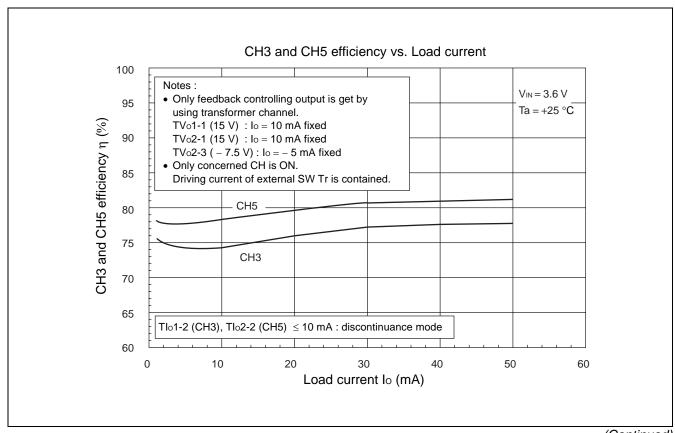
Note: SANYO: SANYO Electric Co., Ltd.

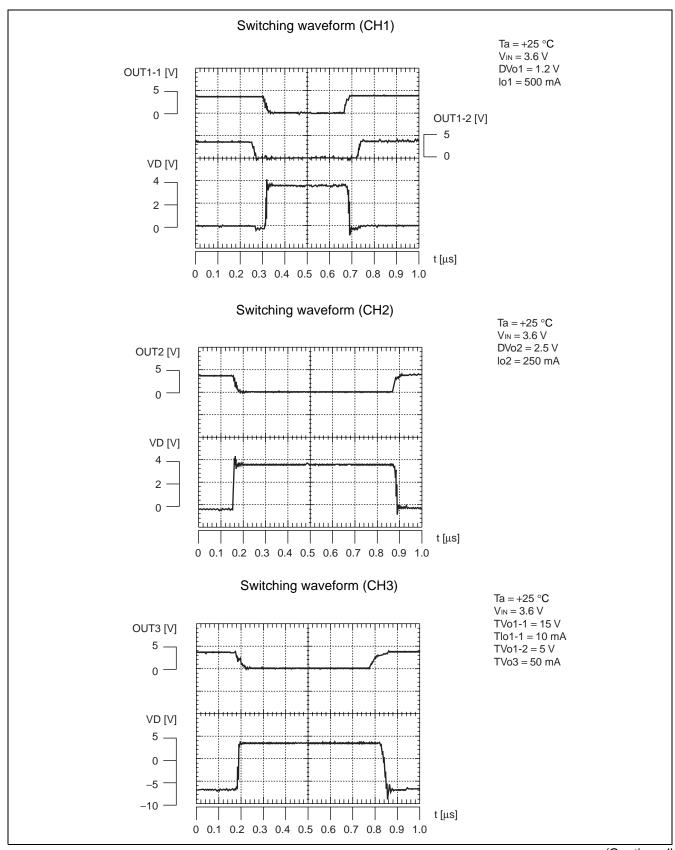
TDK : TDK Corporation SUMIDA : Sumida Corporation ssm : SUSUMU CO., LTD.

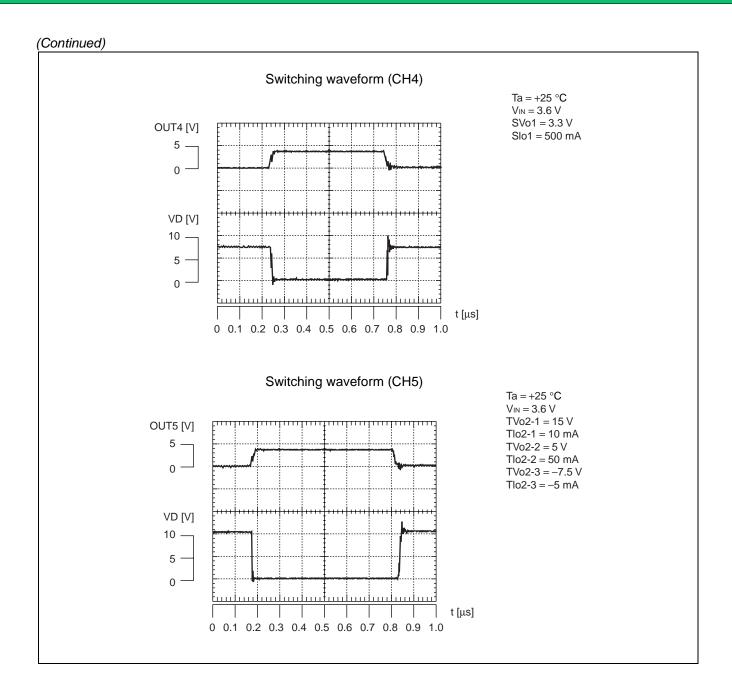
■ REFERENCE DATA











MB39A108

■ USAGE PRECAUTIONS

- Printed circuit board ground lines should be set up with consideration for common impedance.
- Take appropriate static electricity measures.
 - Containers for semiconductor materials should have anti-static protection or be made of conductive material.
 - After mounting, printed circuit boards should be stored and shipped in conductive bags or containers.
 - Work platforms, tools, and instruments should be properly grounded.
 - Working personnel should be grounded with resistance of 250 k Ω to 1 M Ω between body and ground.
- · Do not apply negative voltages.
 - The use of negative voltages below -0.3 V may create parasitic transistors on LSI lines, which can cause malfunction.

■ ORDERING INFORMATION

Part number	Package	Remarks
MB39A108PFT-□□□E1	38-pin plastic TSSOP (FPT-38P-M03)	Lead Free version
MB39A108PV2-□□□E1	40-pin plastic BCC (LCC-40P-M07)	Lead Free version

■ EV BOARD ORDERING INFORMATION

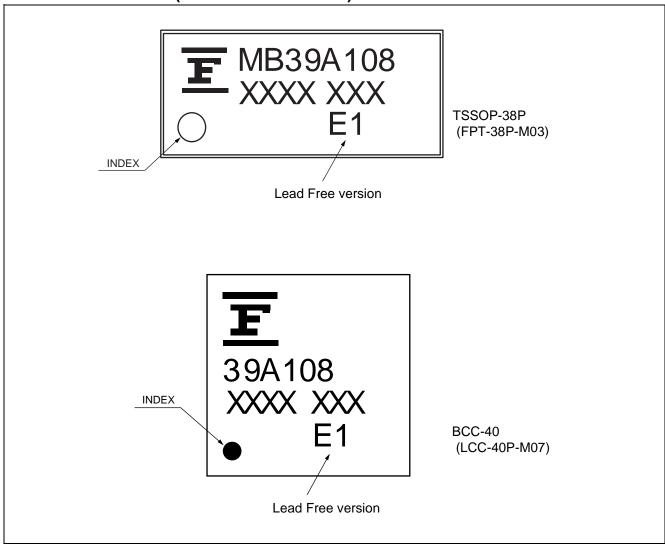
EV board part No.	EV board version No.	Remarks
MB39A108EVB-01	Board Rev. 1.0	TSSOP-38P

■ Rohs Compliance Information of Lead (Pb) Free Version

The LSI products of Fujitsu Microelectronics with "E1" are compliant with RoHS Directive, and has observed the standard of lead, cadmium, mercury, Hexavalent chromium, polybrominated biphenyls (PBB), and polybrominated diphenyl ethers (PBDE).

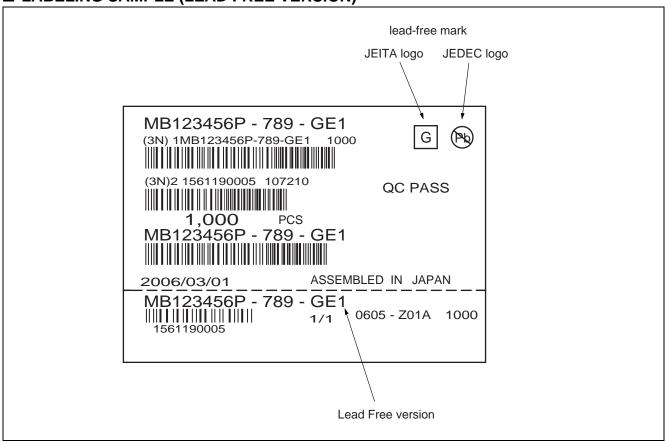
The product that conforms to this standard is added "E1" at the end of the part number.

■ MARKING FORMAT (LEAD FREE VERSION)



MB39A108

■ LABELING SAMPLE (LEAD FREE VERSION)

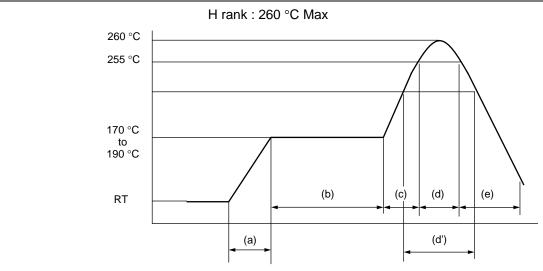


■ MB39A108PFT-□□□E1 (TSSOP-38P) RECOMMENDED CONDITIONS OF MOISTURE SENSITIVITY LEVEL

Item	Condition		
Mounting Method	IR (infrared reflow), Manual soldering (partial heating method)		
Mounting times	2 times		
Storage period	Before opening	Please use it within two years after Manufacture.	
	From opening to the 2nd reflow	Less than 8 days	
	When the storage period after opening was exceeded	Please processes within 8 days after baking (125 °C, 24H)	
Storage conditions	5 °C to 30 °C, 70%RH or less (the lowest possible humidity)		

[Temperature Profile for FJ Standard IR Reflow]

(1) IR (infrared reflow)



(a) Temperature Increase gradient $\,$: Average 1 $^{\circ}\text{C/s}$ to 4 $^{\circ}\text{C/s}$

(b) Preliminary heating : Temperature 170 °C to 190 °C, 60 s to 180 s

(c) Temperature Increase gradient $\,$: Average 1 $^{\circ}\text{C/s}$ to 4 $^{\circ}\text{C/s}$

(d) Actual heating : Temperature 260 °C Max; 255 °C or more, 10 s or less

(d') : Temperature 230 °C or more, 40 s or less

or

Temperature 225 °C or more, 60 s or less

or

Temperature 220 °C or more, 80 s or less

(e) Cooling : Natural cooling or forced cooling

Note: Temperature: the top of the package body

(2) Manual soldering (partial heating method)

Conditions: Temperature 400 °C Max

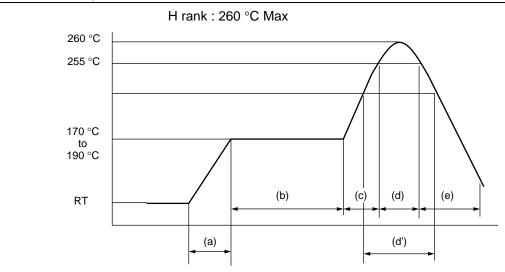
Times : 5 s max/pin

■ MB39A108PV2-□□□E1 (BCC-40) RECOMMENDED CONDITIONS OF MOISTURE SENSITIVITY LEVEL

Item	Condition		
Mounting Method	IR (infrared reflow), Manual soldering (partial heating method)		
Mounting times	2 times		
Storage period —	Before opening	Please use it within two years after	
	From opening to the reflow	Manufacture.	
Storage conditions	5 °C to 30 °C, 70%RH or less (the lowest possible humidity)		

[Temperature Profile for FJ Standard IR Reflow]

(1) IR (infrared reflow)



(a) Temperature Increase gradient : Average 1 °C/s to 4 °C/s

(b) Preliminary heating : Temperature 170 °C to 190 °C, 60 s to 180 s

(c) Temperature Increase gradient : Average 1 °C/s to 4 °C/s

(d) Actual heating : Temperature 260 °C Max; 255 °C or more, 10 s or less

(d') : Temperature 230 °C or more, 40 s or less

or

Temperature 225 °C or more, 60 s or less

or

Temperature 220 °C or more, 80 s or less

(e) Cooling : Natural cooling or forced cooling

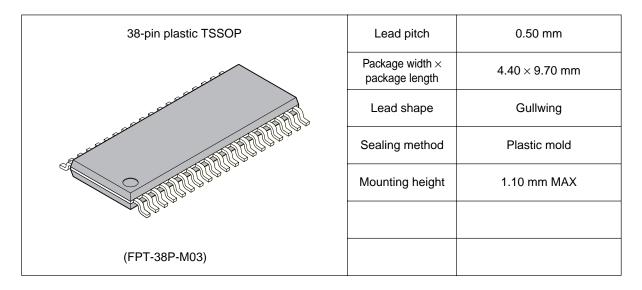
Note: Temperature: the top of the package body

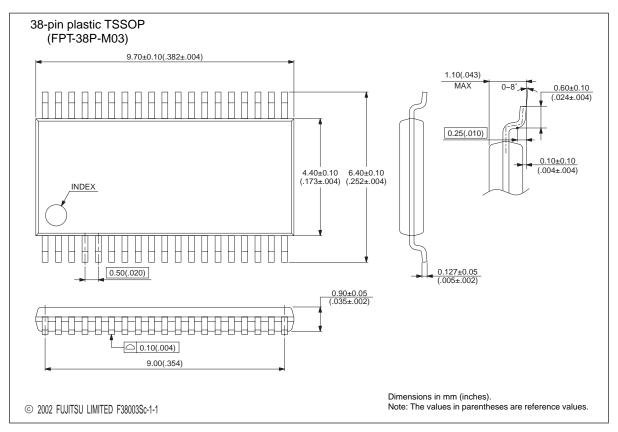
(2) Manual soldering (partial heating method)

Conditions: Temperature 400 °C Max

Times : 5 s max/pin

■ PACKAGE DIMENSION

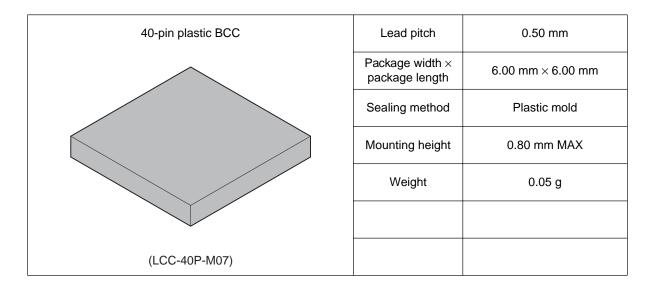


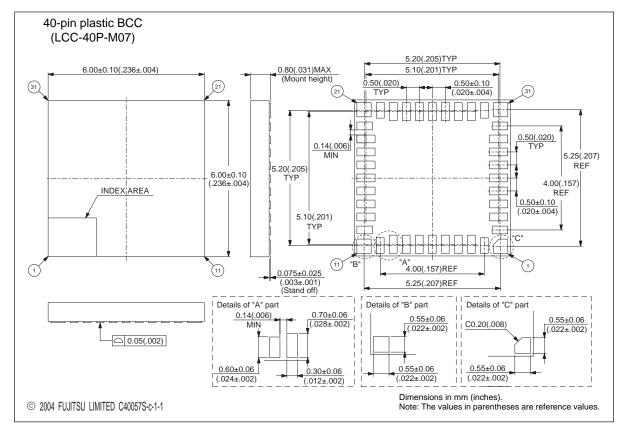


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